

BIO-DATA



Name : DR. JATINDRA NATH ROY

Date of Birth : 12th June 1957

Address : Qtr No.: B-200
IIT Campus, Kharagpur
P.O.: Kharagpur Technology
Dist. Paschim Medinipur
Pin - 721302
Mobile: +91 9679043090
E-mail: jatinroy2000@gmail.com

Academic Qualifications:

Ph.D in Materials Science: Sept. 1980 to Jan 1984 from IIT-Kharagpur.

D.I.I.T in Industrial Physics: 1980 from IIT- Kharagpur

M.Sc. (Physics): 1979 from IIT – Kharagpur

Professional Profile:

Since March 2014:

Visiting Professor (ATDC & SESE) : IIT-Kharagpur

Joint faculty in ATDC (Advance Technology Development Centre) and SESE (School of Energy Science & Engineering). ATDC is engaged in multi-disciplinary research in the area of Microelectronics, MEMS and other related Materials and Devices. SESE is a new initiative of IIT-Kharagpur in the area of Energy, including Renewable Energy such as Solar PV. I have been instrumental to start research programs, including Ph. D., and a PG Course (M. Tech in Energy).

July 2008 to Feb 2014:

Senior Vice President (R&D/Engineering/Quality/Reliability): Solar Semiconductor-Hyderabad. Solar Semiconductor is a Photo-Voltaic (PV) Company engaged in Cell & Module manufacturing and PV Systems for off-grid/Grid Interactive & Utility Scale power plants. I was a part of Senior Management team and responsible for R&D, Engineering,

Technology, Quality, Certification and Reliability related activities of the entire organization. I was a key player for setting up a state of the art facility located at Fab City for Cell and Module Manufacturing equipped with full-fledged Reliability Lab.

September 2006 to July 2008:

During this period, I was with **Semi-Conductor Laboratory (SCL), previously known as Semiconductor Complex Limited (SCL), as Scientist/Engineer: “G”**. I was responsible for complete VLSI operation (Process Technology Development, VLSI design, VLSI & MEMS Manufacturing, Testing and Assembly). I was part of the core team engaged in an upgradation plan with total financial outlay of about \$250M. The details were worked out, vendor selection was done and a draft agreement finalized.

October 2004 to September 2006:

I was **Professor (Microelectronics) under “Faculty of Engineering” in Panjab University-Chandigarh** during this period. I was course co-ordinator for M.Tech (Microelectronics) and M.Tech (Nanoscience & Nanotechnology) courses. I was involved in teaching and research in the area of IC fabrication, Device modeling, Circuit simulation & modeling, Analog & Mixed Signal design and Nanoelectronics.

January 1984 to October 2004:

This was my first employment immediately after completing Ph.D. I was with **Semiconductor Complex Limited (SCL); joined as Senior Engineer (R&D) and was General Manager (R&D and Design) when left**. I was a part of Senior Management team and a key member of a team responsible for setting up a 6 inch VLSI facility including wafer fabrication, Design, assembly, test and QA/QC with an investment of about \$100M. I was responsible for the development of several high end technologies, such as CMOS, EEPROM, High Voltage CMOS, Rad Hard, CCD, MEMS, etc. I was also responsible for the development of special products such as CCD imagers, ASICs as well as several standard products. I had worked in reputed foreign foundries and have joint collaboration projects with several organizations in India and abroad.

Membership/Reccognition/Award

Fellow: Indian National Academy of Engineering (FNAE)

Distinguished Visiting Professor: INAE

Member of INAE Sectional Committee

Senior Member: IEEE (SMIEEE)

Fellow-IMS (Indian Microelectronics Society)

Secretary for three consecutive years of IMS

Honorary Chair of IEEE Chandigarh Sub-section

Honorary Vice Chair of IEEE Hyderabad Section

Best innovator award from EDN-Asia in Nov 1996

Consultant (2005-2006) to Analog Integration Corporation (AIC) – USA

Expert committee member of CDN Live 2006 & 2007 of Cadence.

Conducted Corporate Training for Cypress- India and Cypress-Philippines

Key member of organizing team for several conferences/workshops including Five IMS

Conferences

Guest faculty for various reputed Institutions

Part of Scientific Committee: EUPVSEC-2012 (Frankfurt, Germany) and EUPVSEC-2013 (Paris, France) and EUPVSEC-2015 (Hamburg, Germany)

BOOK

1. **J.N.Roy** and D.K.Syal: Editor of "Trends in VLSI and Embedded Systems": Macmillan Advanced Research Series: 2007
2. **J.N.Roy** and D.N.Bose: Introduction to VLSI Design and Technology: New Age International Publishers, 2010.

PUBLICATIONS:

1. **J.N.Roy**, S.Basu and D.N.Bose: Low Temperature Growth of Poly Crystalline Indium Phosphide; Solar Energy Materials 5(4), 379, (1981).
2. **J.N.Roy**, S.Basu and D.N.Bose: Grain Size Dependence of Mobility in Poly Crystalline n-Indium Phosphide: Journal of Applied Physics 54 (2), 395, (1983).
3. **J.N.Roy**, S.Basu, D.N.Bose and A.J.Singh: Behavior of Large Grain Polycrystalline n-indium Phosphide Grown by SSD Technique: Indian Journal of Pure and Applied Physics 21(70) 395(1983).
4. D.N.Bose, **J.N.Roy** and S.Basu: Improved Schottky Barrier Height on n-Indium Phosphide by Surface Modification: Materials Letters 5B, 455, (1984).
5. **J.N.Roy**, Harish K. Chaudhury and M.J.Zarabi: Effects of Field Implants on Small Geometry CMOS devices: Microelectronics and Reliability 27(6), 953, (1987).
6. **J.N.Roy**, H.C.Mohanty, Bharat Bhushan, M.V.R.Yogi, P.A.Govindacharyulu, D.N.Singh and M.J.Zarabi: Development of 2 μ m CMOS Process: Electronics Today, Aug 1988.
7. **J.N.Roy**, S.Basu and D.N.Bose: Characterisation of Grain Boundary in Polycrystalline n-InP Grown by Gradient-Freeze Method: Materials Letters 7, 359, (1989)
8. **J.N.Roy**: Bulk Growth of Polycrystalline Indium Phosphide: Bulletin of Materials Sciences 13(1), 3(1990).
9. **J.N.Roy**, S.Basu and D.N.Bose: Characterization of n-InP Crystals Grown by Gradient Freeze Method of Different Phosphorus Vapour Pressures: Indian Journal of Pure and Applied Physics 29, 555, (1991).
10. **J.N.Roy** and M.J.Zarabi: Materials for VLSI Processes: IETE Journal of Research: Special Issue on Materials for Electronics: 43 (2&3), March-June 1997, PP 207-213.
11. D.K.Pal, S.M.Pandey, H.Jain and **J.N.Roy**: Model for Metal Interconnection Design Rule Optimization: Microelectronics Engineering 56(2001) 295-302.
12. **J.N.Roy**, S.Basu and D.N.Bose: Growth of Indium Phosphide and Application in PEC Solar Cells: Proceedings of "International Workshop on the Properties of the Physics of Semiconductor devices", Held at Indian Institute of Technology-Delhi (India), Nov 1981.

13. Y. Ramprakash, **J.N.Roy**, S.Basu and D.N.Bose: n-PEC Solar Cells in Presence of Ruthenium Ions: Proceedings of "Solar Energy congress, International Solar energy Society", Held at Perth (Australia) 1983.
14. **J.N.Roy**, S.Basu and D.N.Bose: Grain Boundary Studies in n-Indium Phosphide: Proceedings of "International Symposium on Compound semiconductors and Related Technology", Held at Indian Institute of Technology-Madras (India), Sept. 1983.
15. **J.N.Roy**, S.Basu and D.N.Bose: Growth and Characterization of Indium Phosphide: Proceedings of "International Symposium on Compound Semiconductors and Related Technology", Held at Indian Institute of Technology-Madras (India), Sept.1983.
16. **J.N.Roy and M.J.Zarabi**: Characterization of Ion Implanted Silicon-A Review: Proceedings of "International Symposium of Semiconductor and Fibre Optics Communication", Held at CSIO, Chandigarh (India), Nov.1985.
17. S.Basu, **J.N.Roy** and D.N.Bose: Contact Behavior of Some Metals and Alloys on SSD Grown n-Indium Phosphide: Proceedings of "European Materials Research Society Conference", Held at Strasbourg (France), June 1986.
18. **J.N.Roy** and M.J.Zarabi: The Effect of Sub-threshold Conduction in Low Voltage Small Geometry CMOS Process: Proceedings of "International Symposium of Electronics Devices, Circuits and Systems", Held at IIT-Kharagpur (India) Dec. 87.
19. **J.N.Roy** and M.J.Zarabi: Control of Threshold Voltage and Body Factor of n-Channel Transistor Fabricated by Twin-tub CMOS Technology: National Conference on Electronic Circuits and Systems, Held at University of Roorkee (India), Nov 1989.
20. **J.N.Roy** and Rajesh Mehta: On Multilevel Metal Technology for 1.2 μ m CMOS Process: National Symposium on Advances in Microelectronic Devices and Fabrication Technology: Held at CSIO-Chandigarh (India) Nov.1992.
21. D.Dev and **J.N.Roy**: Fabrication of Oxide Sidewall Spacer for LDD structure: National Symposium on Advances in Microelectronic Devices and Fabrication Technique: Held at CSIO-Chandigarh (India): Nov 1992.
22. **J.N.Roy** and Vinod Chaku Optimization of Tub Design in Twin Tub Based CMOS Process: Proceedings of "International Workshop on Physics of Semiconductor Devices-93", Held at NPL-Delhi in Dec. 1993.
23. **J.N.Roy**, D.K.Datta, R.Rajagopal, Vinod Chaku and D.Dev: Contact Resistance Improvement by Barrier Metal and SALICIDE Technology: Proceedings of "International Workshop on Physics of Semiconductor Devices 93", Held at NPL-Delhi in Dec. 1993.
24. P.R.Verma, A. Bandyopadhyay and **J.N.Roy**: and High Voltage MOS Structures Compatible to Low Voltage CMOS process: Proceedings of "International workshop on Physics of Semiconductor Devices 95" Held at NPL-Delhi in Dec. 95.
25. Vinod Chaku, **J.N.Roy**, Krishna Kumar and Rajesh Goyal: Effect of Dielectric Layer on Top of Silicon surface on Responsivity of Different Photodiodes: Proceedings of "International workshop on Physics of Semiconductor Devices 95" Held at NPL-Delhi in Dec. 95.

26. G.K.Bhaumik, N.Ravi Kumar and **J.N.Roy**: Optimization of Reflection Loss of On-Chip Silicon Photodiode: Proceeding of "International Workshop on Physics of Semiconductor Devices" Held at Delhi, in Dec 97.
27. A.Datta, H.D. Banerjee and **J.N.Roy**: The Effect of TiN/TiSi₂ Bi-layer on Sheet and Contact Resistance in 1.2μm CMOS Technology: Proc. of "The International Conference on Computers and Devices for Communication (CODEC-98)", Held at Calcutta in 1998.
28. S.M.Pandey, H.Jain, D.K.Pal and **J.N.Roy**: Realization of Diffusion to Poly Capacitor in Salicide Based CMOS process: Proc. of "International Workshop on Physics of Semiconductor Devices" Held at New Delhi in Dec. 1999.
29. S.M.Pandey, N.Ravi Kumar, G.K.Sankar, D.K.Pal and **J.N.Roy**: Optimization of Dual Poly Gate Low Voltage CMOS Process: Proc. of "International Workshop on Physics of Semiconductor Devices" Held at New Delhi Dec. 1999.
30. N.Ravi Kumar, G.K.Sankar, **J.N.Roy** and D.N.Singh: Design and Realization of High performance CMOS Compatible Lateral Bipolar Transistors. (CLBTS). Proc. of "International Workshop on Physics of Semiconductor Devices" Held at New Delhi in Dec. 1999.
31. S.S.Kullar, S.Das Gupta, D.K.Mallik and **J.N.Roy**: Optimized Output Structures for Visible Imager Charge Coupled Devices. Proc. of "International Workshop on Physics of Semiconductor Devices" Held at New Delhi in Dec. 1999.
32. Upinder Singh, Nurul Islam, Arvind Kumar and **J.N.Roy**: Optimization of Field Plated LDMOS for High Voltage Operation. Proc. of "International Workshop on Physics of Semiconductor Devices" Held at New Delhi in Dec. 1999.
33. A.Datta, H.D. Banerjee and **J.N.Roy**: Modeling of Polysilicon Depletion Effect in Submicron CMOS Performance. "International Conference on Communications, Computers & Devices" Held on Dec. 14-16, 2000, at IIT- Kharagpur
34. Upinder Singh and **J.N.Roy**: Realization of High Gain (Collector Isolated) Vertical NPN Transistor in a Standard CMOS Process: "International Conference on Communications, Computers & Devices" Held on Dec. 14-16, 2000, at IIT Kharagpur
35. S. Sarkar, J.C.Santiard, V.Sharma, **J.N.Roy** and **S.K.Sen**: A Low Noise CMOS Analog Digital Signal Process for Dimuon Spectrometer of ALICE in LHC: "Proc. of VLSI 2001" Held on Sept. 2001 at Roorkee University.
36. D.K.Pal, J.Guha, H.Jain, K.Shankar and **J.N.Roy**: Optimization of Local Oxidation Of Polysilicon over Silicon Isolation Structure (LOCOS): Proc. Of "International Workshop of Physics on Semiconductor Devices" Held at New Delhi in Dec. 2001.
37. Upinder Singh, Deo Brat Singh and **J.N.Roy**: Implementation of Optimized Vertical Bipolar Transistor in CMOS process Technology: Proc. Of "International Workshop of Physics on Semiconductor Devices" Held at New Delhi in Dec. 2001.
38. Dilip K. Routray and **J.N.Roy**: Low Power Analog Design: Chandigarh Synoposium on Microelectronics (CSME), Held at PU, Chandigarh, Feb.2001.
39. D.K.Pal, H. Jain and **J.N.Roy**: Modeling of Current Carrying Capacity of Metal Interconnect: Chandigarh Synoposium on Microelectronics (CSME), Held at PU, Chandigarh, Feb.2001.

40. A.Dixit, D.K.Pal, **J.N.Roy** and V.Ramgopal Rao: Channel Engineering for Sub-Micron CMOS Technology: Proc. Of “International Workshop of Physics on Semiconductor Devices” Held at New Delhi in Dec. 2001.
41. Vivek Tripathi and **J.N.Roy**: Design of Sigma-Delta ADC: Chandigarh Synposium on Microelectronics (CSME), Held at PU, Chandigarh, Feb.2001.
42. Satadru Sarkar, Chumki Saha and **J.N.Roy**: Study of MOSFET Model Validation for BSIM & BSIM3 Models in 0.8um CMOS Technology: Proc. of “International Workshop of Physics of Semiconductor Devices” Held at Chennai in Dec. 2003.
43. Upinder Singh, Himanshu Jain and **J.N.Roy**: Realization of High Resistive Poly Resistor in Standard CMOS Process: Proc. of “International Workshop of Physics of Semiconductor Devices” Held at Chennai in Dec. 2003.
44. Vinita Mishra, B.Umapathi, Sudipto Das Gupta, Vikram Singh and **J.N.Roy**: Design of Multi-Phase Pinned (MPP) CCD Imaging Device for Optimum Performance: Proc. of “International Workshop of Physics of Semiconductor Devices” Held at Chennai in Dec. 2003.
45. Upinder Singh, Deo Brat Singh and **J.N.Roy**: HSPICE Compatible Model for N-channel LDMOS: Proc. of “International Workshop of Physics of Semiconductor Devices” held at Chennai in Dec. 2003.
46. B. Umapathi, S.Das Gupta and **J.N.Roy**: Advanced CCD Image Sensors: Chandigarh Symposium on Microelectronics (CSME), Held at PU, Chandigarh, Feb.2003.
47. **J.N.Roy**: Output Structure for Visible Imager Charge Coupled Devices: Invited Talk in VLSI Design and Test (VDAT) Conference-2003.
48. D.K.Routray, Deep Sehgal and **J.N.Roy**: Micropower Programmable Voltage Multiplier: Chandigarh Symposium on Microelectronics (CSME), Held at PU, Chandigarh, Feb.2003.
49. Deepak K. Syal and **J.N.Roy**: Embedded Systems and MEMS Structures for Tactile Displays: IMS Conference-2005, Held at Chandigarh in Feb,2005.
50. **J.N.Roy**: Nanoelectronics Device: Issues and Options: National Seminar on Information Technology-Recent Advances & Applications (ICT-2006), Held at JMIT-Radaur, Feb.2006
51. Rahul K. Singh and **J.N.Roy**: Modeling of N-Well device and N-well Field Resistor: Solid State Electronics : Vol 50, 1696-1704, 2006
52. Anita Kumari and **J.N.Roy**: Low power 7T SRAM cell Scheme- “Saving Write Zero Power”: Conference and Exhibition on IP-SOC 2006: IP based SOC Design, Held at Grenoble- France, Dec.2006
53. **J.N.Roy**: Silicon On Insulator (SOI) Technology- An Overview: Proc. Of IMS Coference-2007, Held at Punjab Engineering College – Chandigarh in Aug.2007.
54. B.Umapathi, Sudipto Das Gupta, Vinita Mishra, Priya Hira and J.N.Roy: Design And Development of 1K × 1K Frame Transfer Imager: Proc. Of “Satellite Technology Day 2007”
55. Munish Mallik and **J.N.Roy**: Design of Low Voltage Differential Signaling (LVDS) Transmitter for Operation at 100 Mbps: Proc. Of IMS Coference-2007, Held at Punjab Engineering College – Chandigarh in Aug.2007.
56. Deep Sehgal and **J.N.Roy**:The design and Development of a High Performance Read-Out Integrated Circuit for Infrared Focal Plane Array: Proc. Of IMS

- Coference-2007, Held at Punjab Engineering College (PEC) – Chandigarh in Aug.2007.
57. **J.N.Roy** Charge Coupled Device (CCD) Imagers: “Annals of INAE-2007”; an INAE Journal
 58. **J.N.Roy** Nanotechnology and Nanocomputing: Recent Advances and Trends in Electrical Engineering, Held at NITTTR-Chandigarh in Feb.2008.
 59. Manoj Wadhwa, Manish Hooda, Sanjay Verma and **J.N.Roy**: Micro Electro Mechanical Systems (MEMS)- a Technological Revolution: Recent Trends in Electronics and Communication: SUSCET-Mohali in April.2008.
 60. Ayan Karmakar, Kamaljeet Singh, Manoj Wadhwa, Sanjay Verma and **J.N.Roy**: Characterization of Conductor backed finite ground co-planar waveguide: Recent Trends in Electronics and Communication: SUSCET_Mohali in April 2008.
 60. Ashutosh Yadav, Rahul K. Tripathi, Rajesh K. Srivastava, Praveen Rana, H.S.Jatana and **J.N.Roy**: A 12-bit 1 Msample/s Pipelined Analog-to-Digital Converter: Proc. Of “Satellite Technology Day 2008”
 61. Amit Chaudhry and **J.N.Roy**: Impact of Energy Quantization and Poly Depletion Effect on CV Analysis and Threshold Voltage of a n-MOSFET: International Conference on Semiconductor Electronics, ICSE-08, held in Malaysia, Oct. 2008.
 62. Amit Chaudhry and **J.N. Roy**: “Modeling of Gate Leakage Current in High-K Dielectrics”: Proceedings of 32nd IEEE International Convention on Information and Communication Technology, Electronics and Microelectronics, MIPRO, 2009 at Croatia, May, 2009, pp 79-84.
 63. Amit Chaudhry and **J.N.Roy**: Analytical Modeling of Quantum Mechanical Tunneling in MOSFET: Proceeding of IEEE- Regional Symposium on Microelectronics (RSM), Malaysia, August, 2009, pp 22-27.
 64. Amit Chaudhry and **J.N. Roy**: Quantum Mechanical Effects in MOSFETS: Journal of World Academy of Science, Engineering and Technology (WASET), Vol 58, 2009, pp 1445-1452.
 65. Amit Chaudhry and **J.N.Roy**: Analytical Modeling of Energy Quantization effects in MOSFET: Proceeding of International Conference Microelectronics and Computer Science, Chisinau, Moldova, Oct. 2009, pp 107-110.
 66. **J.N.Roy**, Govadhan Rao Gariki and Nagalakshmi V.: Reference Module Selection Criteria for Accurate Testing of Photovoltaic (PV) Panels: Solar Energy, Vol.84, pp. 32-36, Jan., 2010.
 67. Amit Chaudhry and **J.N.Roy**: MOSFET Models, Quantum Mechanical Effects and Modeling Approach: A Review: Journal of Semiconductor Science and Technology (JSST), June 2010.
 68. Amit Chaudhry and **J.N.Roy**: Impact of quantum inversion charge centroid on the various parameters of a nano-MOSFET: Accepted for publication in the WASET International Conference on Microelectronic Devices, Rome, Italy, April, 2010.

69. Amit Chaudhry and **J.N.Roy**: Analytical Modeling of Quantum Mechanical Tunneling in Germanium Nano-MOSFET: Journal of Electronic Science and Technology, Vol.8, No.1, March 2010
70. Amit Chaudhry and **J. N. Roy**: Analytical Modeling of depletion and Energy Quantization in Poly Silicon of a Nano-MOSFET: ISC2010 Conference, Budapest, June 2010.
71. Amit Chaudhry and **J.N.Roy**: Analytical Modeling of Source-to-drain Tunneling In Nanoscale Silicon MOSFET: Journal of Electronics Science and Technology, Vol. 8, No. 4, December, 2010
72. Amit Chaudhry and **J.N.Roy**: Inversion Layer Quantization in Arbitrarily Oriented Substrates: An Analytical Study: ELEKTRIKA, Vol.12, No.1, December, 2010
73. Amit Chaudhry and **J.N. Roy**: Quantum Mechanical Direct leakage currents in a sub 10nm MOSFET: A Rigorous modeling study: International Journal of Nanoelectronics and Materials, (Accepted), 2011.
74. Amit Chaudhry and **J.N. Roy**: Analytical modeling of Energy Quantization Effects in nanoscale MOSFETS: International Journal of Nanoelectronics and Materials, (Accepted), 2011.
75. Amit Chaudhry and **J.N. Roy**: Gate oxide leakage in poly-depleted nanoscale-MOSFET: A Quantum Mechanical Study: International Journal of Nanoelectronics and Materials, (Accepted), 2011.
76. Amit Chaudhry, **J.N. Roy** and S. Sangwan: A SPICE Compatible Analytical Electron Mobility Model for Biaxial Strained-Si-MOSFETs: Chinese Journal of Semiconductors, (Accepted), 2011.
77. Amit Chaudhry and **J.N. Roy**: An analytical modeling for quantum mechanical tunneling in nano-p-MOSFETs: Electronics, Vol. 14, No.2, 2010.
78. Amit Chaudhry and **J.N. Roy**: A Comparative Study of Hole and Electron Inversion layer Quantization in MOS Structures: Serbian Journal of Electrical Engineering, Vol. 7, No 2, pp. 185-193, Nov,2010.
79. Amit Chaudhry, Garima Joshi, **J.N. Roy** and D.N. Singh: Strained Silicon MOSFET Structures for Nanoscale Applications: A Review: Acta Technica Napocensis - Electronică și Telecomunicații, Vol.51, No.3, pp.15-22,2010.
80. Amit Chaudhry and **J.N. Roy**: Inversion layer Quantization in Arbitrarily Oriented Substrates: An Analytical Study: Elektrica-UTM Journal of Electrical Engineering, Vol.12, No 1, pp.1-6, 2010.
81. Amit Chaudhry and **J.N. Roy**: Comparative Study of Energy Quantization Approaches in nanoscale MOSFETS: Journal of Electronic Science and Technology, Vol.9, No.1, 2011.
82. Amit Chaudhry and **J.N. Roy**: Mathematical Modeling of MOS Capacitance in the presence of Depletion and Energy Quantization in

- Poly Silicon Gate: Chinese Journal of Semiconductors, Vol.31, No.11, pp. 400-1-400-4, Nov, 2010.
83. Amit Chaudhry, **J.N. Roy** and Garima Joshi: Nanoscale strained-Si MOSFET physics and modeling approaches: A Review: Chinese Journal of Semiconductors, Vol.31, No.10, pp.400-1-400-6, October, 2010.
 84. Amit Chaudhry and **J.N. Roy**: Impact of depletion and doping variation in poly gate and energy quantization in the substrate on gate leakage current in a nano-MOSFET: Proceedings of Prime Asia Conference on Post graduate Research in Microelectronics and Electronics, Shanghai, China, Sept, 2010.
 85. Amit Chaudhry and **J.N. Roy**: Gate capacitance modeling in (100), (110) and (111) oriented nanoscale MOSFET substrates: Proceedings of International Conference on Electrical and Computer Engineering, Dhaka, Bangladesh, Dec, 2010.
 86. KVSR Kishore, Nazini S.K., Ashsih K Singh and **J.N.Roy**: Degradation Mechanism of Crystalline Solar Module from Damp Heat (DH) Test-to-Failure: 38th IEEE Photovoltaic Specialist Conference, June 3-8, 2012, Austin, Texas, USA.
 87. **J N Roy**: Modeling of Insulation Characteristics of Solar Photovoltaic (SPV) Modules: Solar Energy, Vol. 120, pp 1-8, 2015.
 88. Brajesh Kumar, **J N Roy** and Manab Das: Solar Energy Harvesting using Increase Heat Transfer Co-efficient and Absorption Rates, International Conference on Material Science & Technology, New Delhi, 2016, VBRI Press, DOI: 10-5185/icmtech.2016.
 89. **J N Roy**: Comprehensive Analysis and Modeling of Cell to Module (CTM) Conversion Loss During c-Si Solar Photovoltaic (SPV) Module Manufacturing: Solar Energy, Vol. 130, pp 184-192, 2016.

PATENT APPLICATIONS:

- 1, Realization of Isolated Zener Diode in CMOS Process for Surge Protection and Voltage Regulation: **Patent No.: 232362, Application No.:374/DEL/1997, File No.:37/2008**
2. Novel Technique for Realization of Poly Silicon Fuses. **Patent No.:232406, Application No.:679/DEL/1997, File No.:21/2008**
3. A Vertical MOS Structure: **Patent No.: 232383, Application No.: 2625/DEL/1997, File No.:31/2008**
4. Embedded RFID Solution for Solar Panel: **US Patent No: 12/726,496, Publication No.: US2010/0236598 A1, Publication Date: Sept 23, 2010**